



DTV1500UH

(CRT HORIZONTAL DEFLECTION) HIGH VOLTAGE DAMPER DIODE

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	6 A
V_{RRM}	1500 V
$V_F(max)$	1.3 V
$t_{rr}(max)$	125 ns

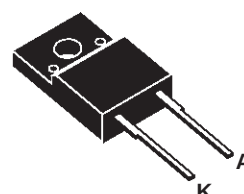
FEATURES AND BENEFITS

- High breakdown voltage capability
- High frequency operation
- Specified turn on switching characteristics
- Very fast recovery diode
- Low static and peak forward voltage drop for low dissipation
- Insulated package
Insulating voltage = 2000V DC
Capacitance = 12pF
- Planar technology allowing high quality and best electrical characteristics

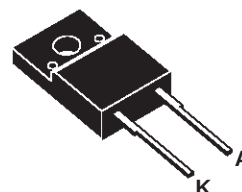
DESCRIPTION

High voltage diode especially designed for horizontal deflection stage in standard and high resolution displays for TV's and monitors.

This device is packaged in ISOWATT220AC and TO-220FPAC (insulated package).



TO-220FPAC
DTV1500UHFP



ISOWATT220AC
DTV1500UHF

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1500	V
$I_{F(RMS)}$	RMS forward current		15	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10ms$ sinusoidal	80	A
T_{stg}	Storage temperature		- 65 to 150	°C
T_j	Maximum operating junction temperature		150	°C

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to Case thermal resistance	TO-220FPAC	4.2	°C/W
		ISOWATT220AC	3.7	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
				Min	Typ	Max	
I_R *	Reverse leakage current	$V_R = 1500V$	$T_j = 25^\circ C$			100	μA
			$T_j = 125^\circ C$		100	1000	μA
V_F **	Forward voltage drop	$I_F = 6A$	$T_j = 25^\circ C$		1.4	1.9	V
			$T_j = 125^\circ C$		1.0	1.3	

pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$ ** $t_p = 380\text{ }\mu s$, $\delta < 2\%$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
				Min	Typ	Max	
t_{rr}	Reverse recovery time	$T_j = 25^\circ C$	$I_F = 1\text{ A}$ $dI_F/dt = -50A/\mu s$ $V_R = 30V$		90	125	ns
t_{rr}	Reverse recovery time	$T_j = 25^\circ C$	$I_F = 100mA$ $I_R = 100mA$ $I_{RR} = 10mA$		600		ns

TURN-ON SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
				Min	Typ	Max	
t_{fr}	Forward recovery time	$T_j = 100^\circ C$	$I_F = 6\text{ A}$ $dI_F/dt = 80\text{ A}/\mu s$ $V_{FR} = 3\text{ V}$			270	ns
V_{Fp}	Peak forward voltage	$T_j = 100^\circ C$	$I_F = 6\text{ A}$ $dI_F/dt = 80\text{ A}/\mu s$		12	18	V

To evaluate the maximum conduction losses use the following equation :

$$P = 1.01 \times I_{F(AV)} + 0.048 \times I_F^2(RMS)$$

Fig. 1: Power dissipation versus peak forward current (triangular waveform, $\delta = 0.45$)

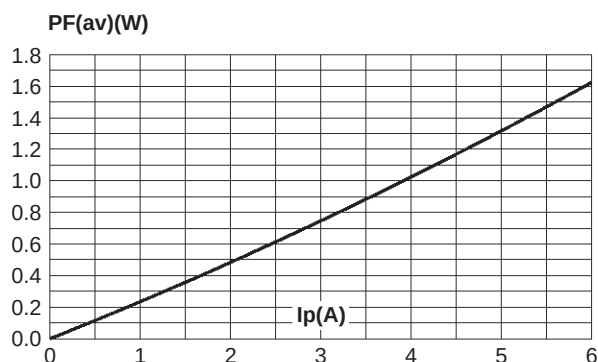


Fig. 2-1: Average current versus case temperature, ($\delta = 0.5$) (TO-220FPAC)

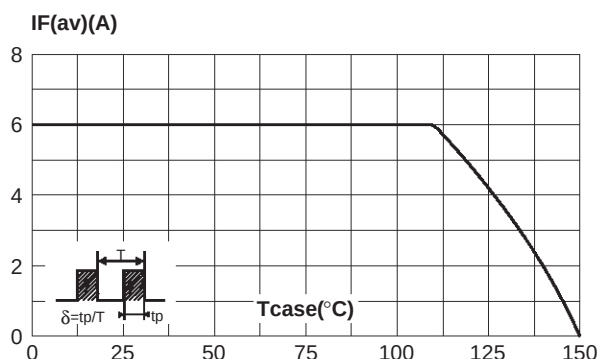


Fig. 2-2: Average current versus case temperature, ($\delta = 0.5$) (ISOWATT220AC)

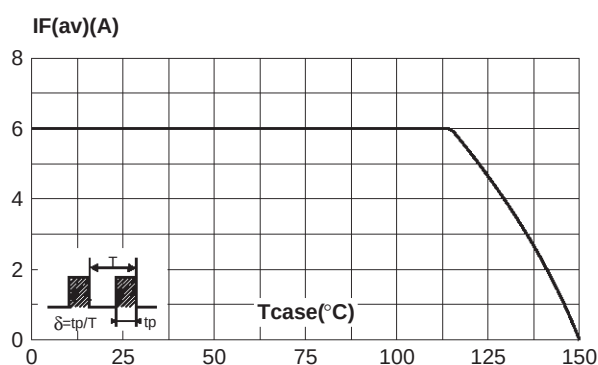


Fig. 3: Forward voltage drop versus forward current (typical values)

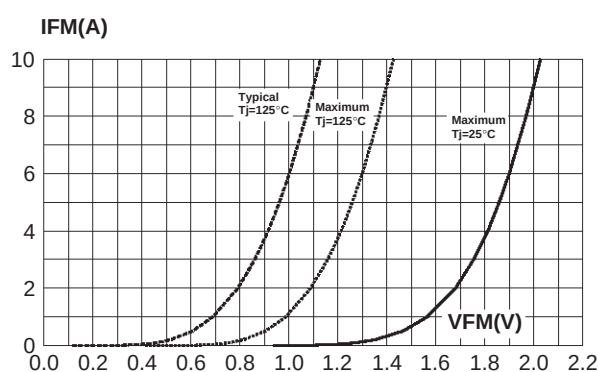


Fig. 4-1: Non repetitive surge peak forward current versus overload duration (TO-220FPAC)

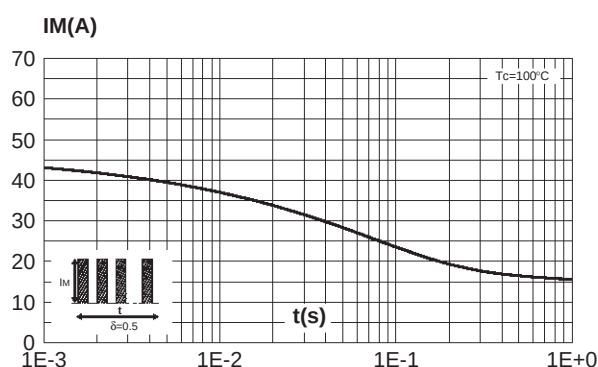


Fig. 4-2: Non repetitive surge peak forward current versus overload duration (ISOWATT220AC)

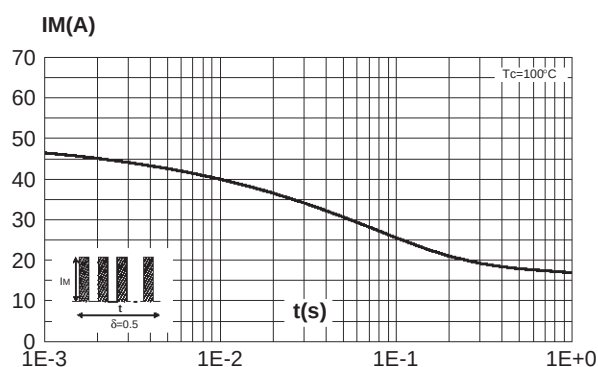


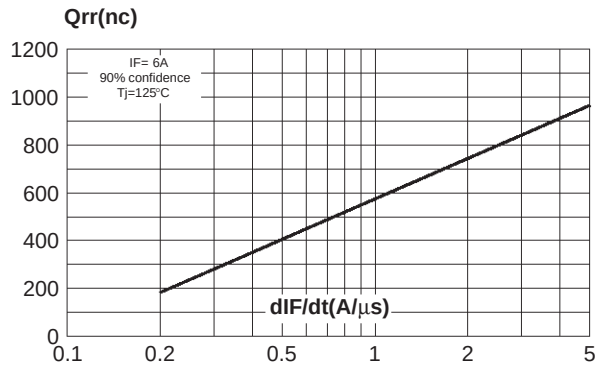
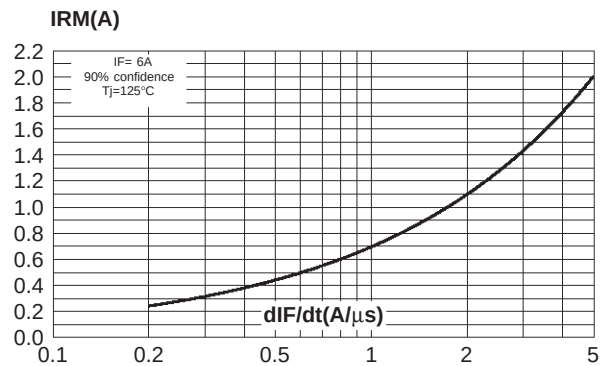
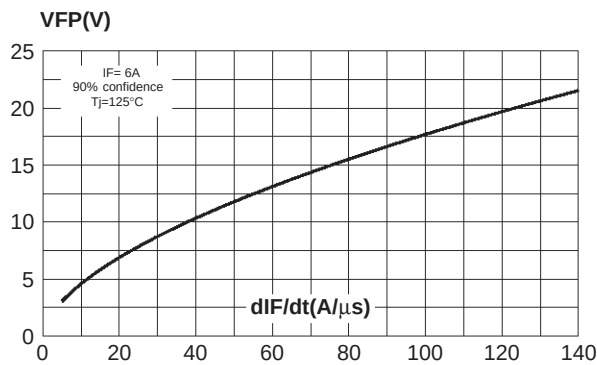
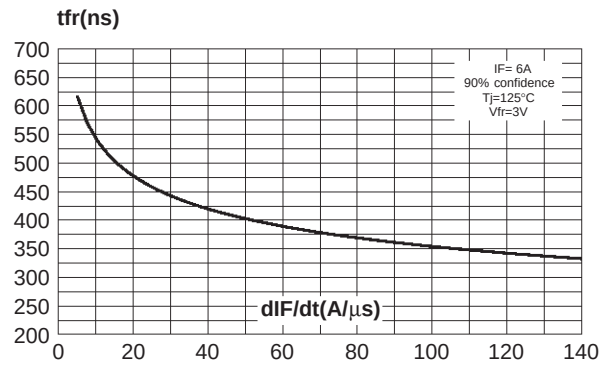
Fig. 5: Reverse recovery charges versus dI_F/dt Fig. 6: Reverse recovery current versus dI_F/dt Fig. 7: Transient peak forward voltage versus dI_F/dt Fig. 8: Forward recovery time versus dI_F/dt 

Fig. 9: Dynamic parameters versus junction temperature

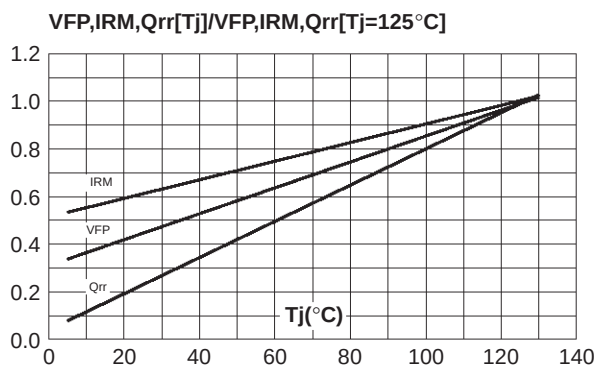


Fig. 10: Junction capacitance versus reverse voltage applied (typical values)

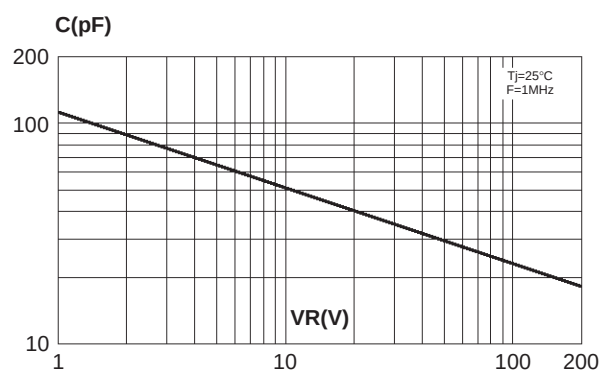
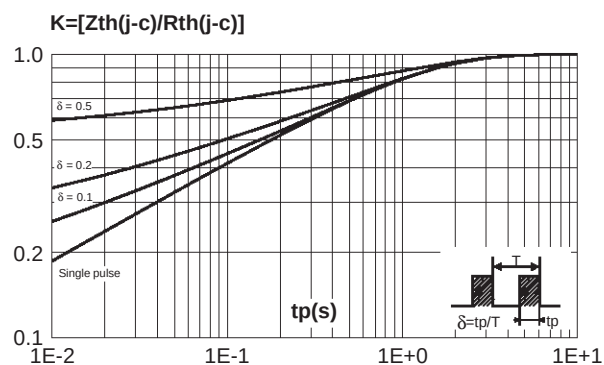
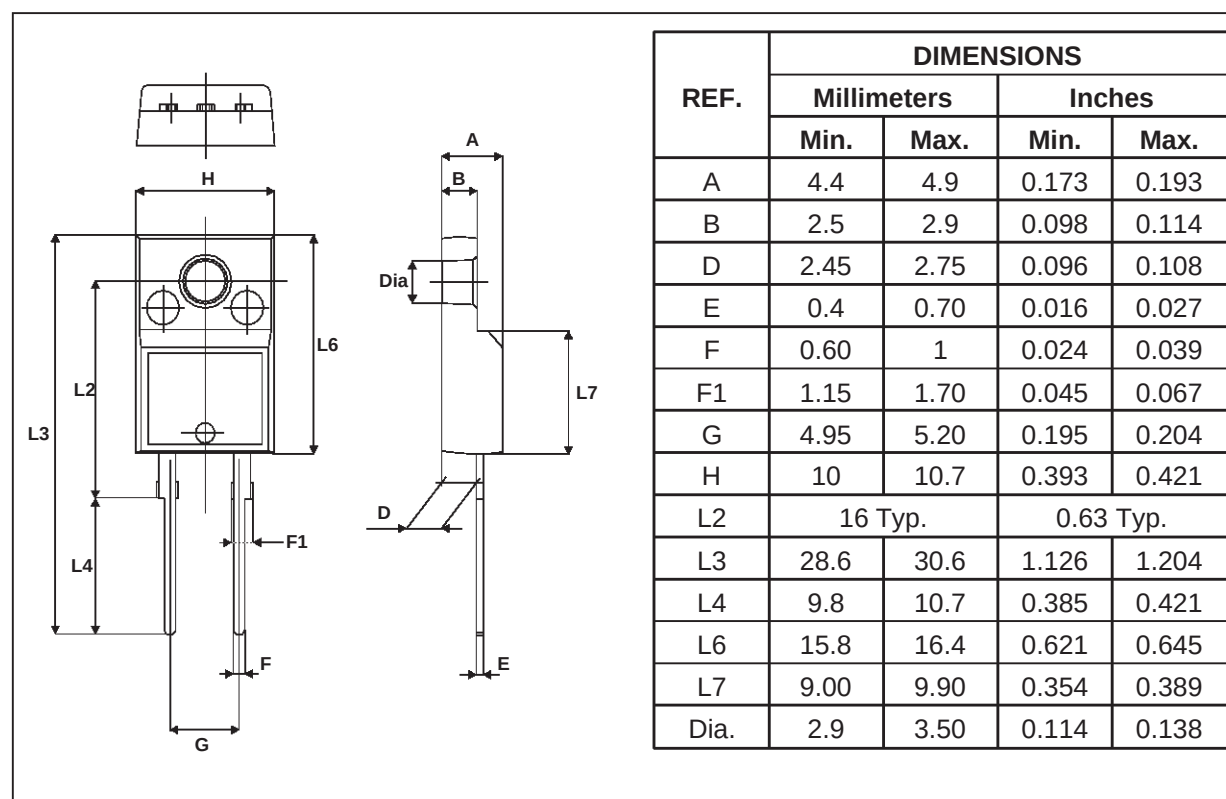
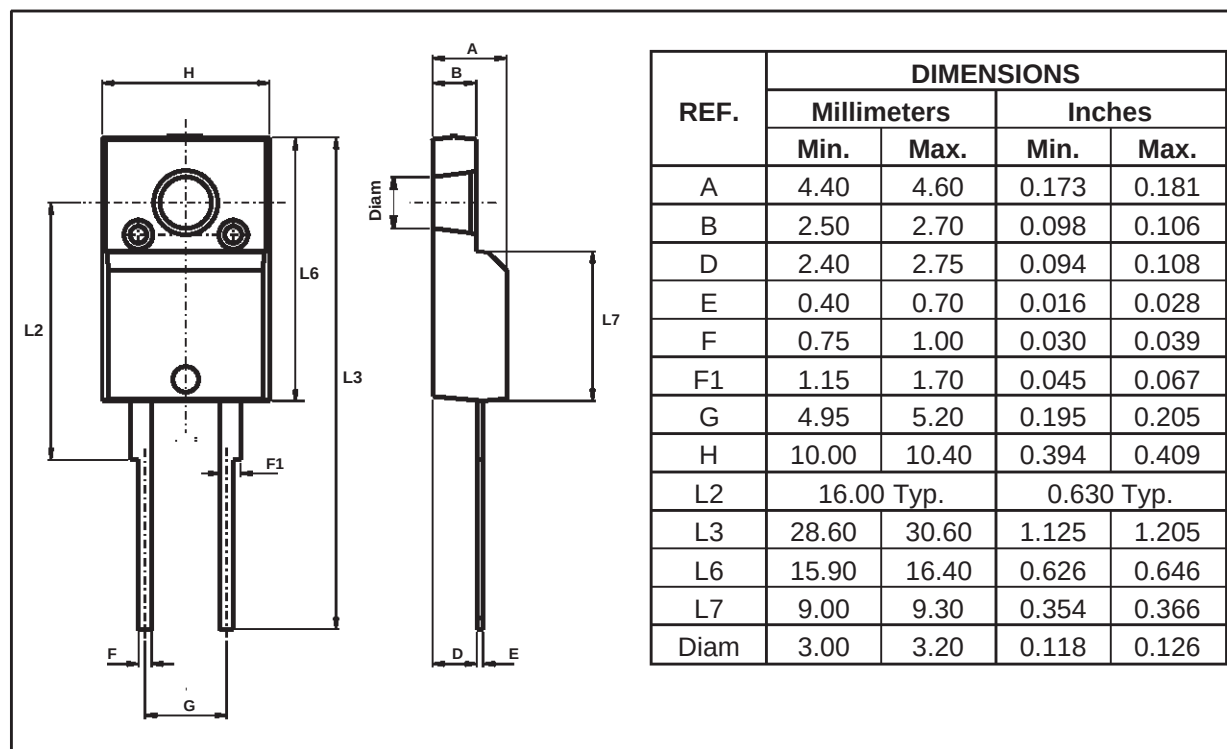


Fig. 11: Relative variation of thermal impedance junction to case versus pulse duration



PACKAGE DATA
TO-220FPAC



PACKAGE DATA
ISOWATT220AC


Type	Marking	Package	Weight	Base qty	Delivery mode
DTV1500UHFP	DTV1500UHFP	TO-220FPAC	1.8g	50	Tube
DTV1500UHF	DTV1500UHF	ISOWATT220AC	2g	50	Tube

- Cooling method: C
- Epoxy meets UL94-V0
- Torquevalue: 0.55 m.Ntyp (0.7m.Nmax)
- Electrical Isolation: 2000V DC
- Capacitance: 12pF

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